





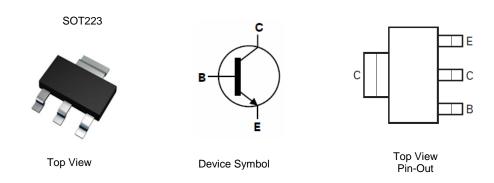
#### **400V NPN HIGH VOLTAGE TRANSISTOR IN SOT223**

#### **Features**

- BV<sub>CEO</sub> > 400V
- I<sub>C</sub> = 500mA High Continuous Current
- I<sub>CM</sub> = 1A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(SAT)</sub> < 250mV @ 50mA
- h<sub>FE</sub> > 40 Specified up to 200mA for High Current Gain Hold-Up
- Complementary PNP Type: FZT758
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
  UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208
- Weight: 0.112 grams (Approximate)



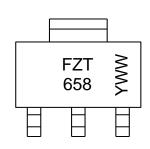
## **Ordering Information** (Note 4)

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FZT658TA	FZT658	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

### **Marking Information**



SOT223

FZT 658 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W$  = Week Code (01~53)



### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	400	V
Collector-Emitter Voltage	V <sub>CEO</sub>	400	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ic	0.5	Α
Peak Pulse Current	I <sub>CM</sub>	1	A

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Power Dissipation	(Note 6)	Б	2.0	W	
Power Dissipation	(Note 7)	$P_{D}$	1.6		
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>θ</sub> JA 62.5 78.1	62.5		
Thermal Resistance, Junction to Ambient	(Note 7)		78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		$R_{ hetaJL}$	12.9		
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

# ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

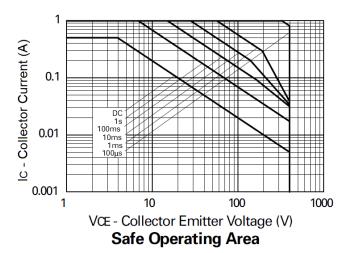
Notes:

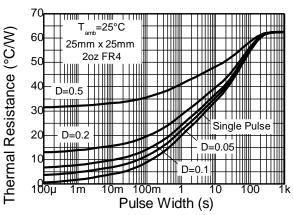
- 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Same as Note 5, except the device is mounted on minimum recommended pad layout.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

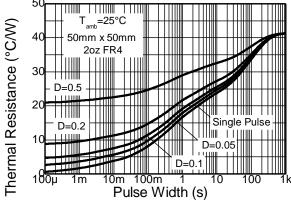




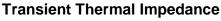
## **Thermal Characteristics and Derating Information**

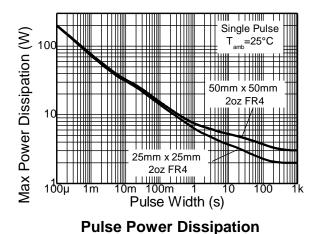


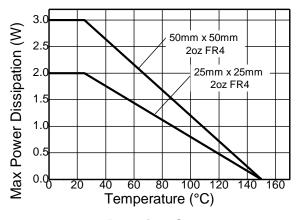




**Transient Thermal Impedance** 







**Derating Curve** 





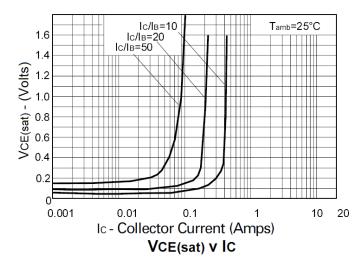
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

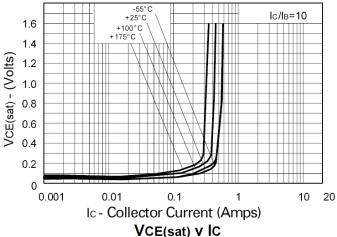
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	400	-	-	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	400	-	-	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	-	-	V	I <sub>E</sub> = 100μA
Collector Cut-Off Current	I <sub>CBO</sub>	-	-	100	nA	V <sub>CB</sub> = 320V
Emitter Cut-Off Current	I <sub>EBO</sub>	-	-	100	nA	V <sub>EB</sub> = 6V
		-	-	0.30	V	$I_C = 20\text{mA}$ , $I_B = 1\text{mA}$
Collector-Emitter Saturation Voltage (Note 9)	V <sub>CE(sat)</sub>			0.25		$I_C = 50$ mA, $I_B = 5$ mA
				0.50		I <sub>C</sub> = 100mA, I <sub>B</sub> = 10mA
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>	-	-	0.9	V	I <sub>C</sub> = 100mA, I <sub>B</sub> = 10mA
Base-Emitter Turn-On Voltage (Note 9)	V <sub>BE(on)</sub>	-	-	1.0	V	I <sub>C</sub> = 100mA, V <sub>CE</sub> = 5V
	h <sub>FE</sub>	50	-	-		I <sub>C</sub> = 1mA, V <sub>CE</sub> = 5V
DC Current Gain (Note 9)		50	-	-	_	I <sub>C</sub> = 100mA, V <sub>CE</sub> = 5V
		40	-	-		I <sub>C</sub> = 200mA, V <sub>CE</sub> = 10V
Current Gain-Bandwidth Product (Note 9)	f <sub>T</sub>	50	-	-	MHz	$V_{CE} = 20V, I_{C} = 10mA,$ f = 20MHz
Output Capacitance (Note 9)	C <sub>obo</sub>	-	10	-	pF	V <sub>CB</sub> = 20V, f = 1MHz
Switching Times	t <sub>on</sub>	-	130	-	no	I <sub>C</sub> = 100mA, V <sub>CC</sub> = 100V
Switching Times	t <sub>off</sub>	-	3,300	=	ns	$I_{B1} = 10 \text{mA}, I_{B2} = -20 \text{mA}$

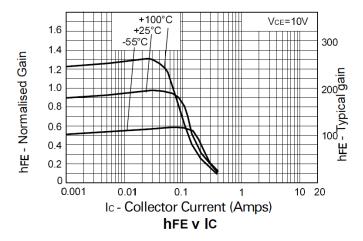
Note: 9. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

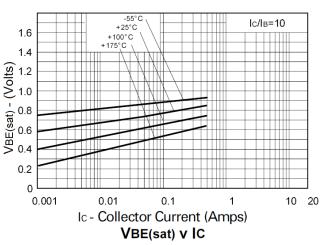


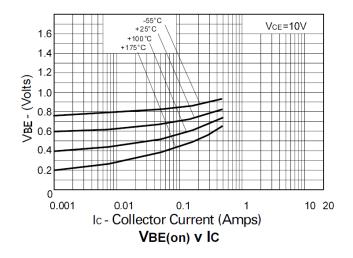
# Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)









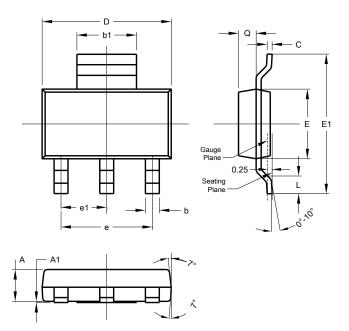






## **Package Outline Dimensions**

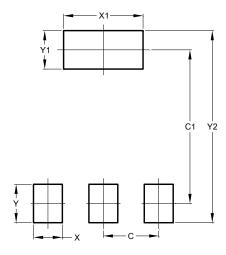
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to voltage spacing between terminals.





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